

Datasheet

180V Three-phase Gate Driver FD6187T

Fortior Technology (Shenzhen) Co., Ltd

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180V Three-phase Gate Driver

1 System Introduction

1.1 Overview

FD6187T is an integrated circuit (IC) that integrates three independent half-bridge gate drivers. It is specially designed for high-voltage and high-speed MOSFET driver applications.

FD6187T supports under-voltage lockout (UVLO) feature, protecting the power tube from operating with insufficient voltage.

FD6187T also provides cross-conduction prevention and deadtime insertion to effectively protect the power IC and prevent both MOSFETs of each half-bridge from switching on at the same time.

FD6187T has built-in input signal filtering module to avoid input noise interference.

1.2 Package



TSSOP20

1.3 Features

- Fully operational to +180V
- Power supply: 5.0V ~ 22V
- Three independent half-bridge drivers
- Output current: +0.8A/-0.8A
- 3.3V/5V logic input compatible
- VCC UVLO
- Cross-conduction prevention logic
- Built-in deadtime module
- Built-in input filtering module
- High-side outputs in phase with inputs, and low-side outputs out of phase with inputs

1.4 Applications

- Electric vehicles, self-balancing vehicles, electric scooters, etc.
- Motor drive applications

1.5 Typical Application Diagram

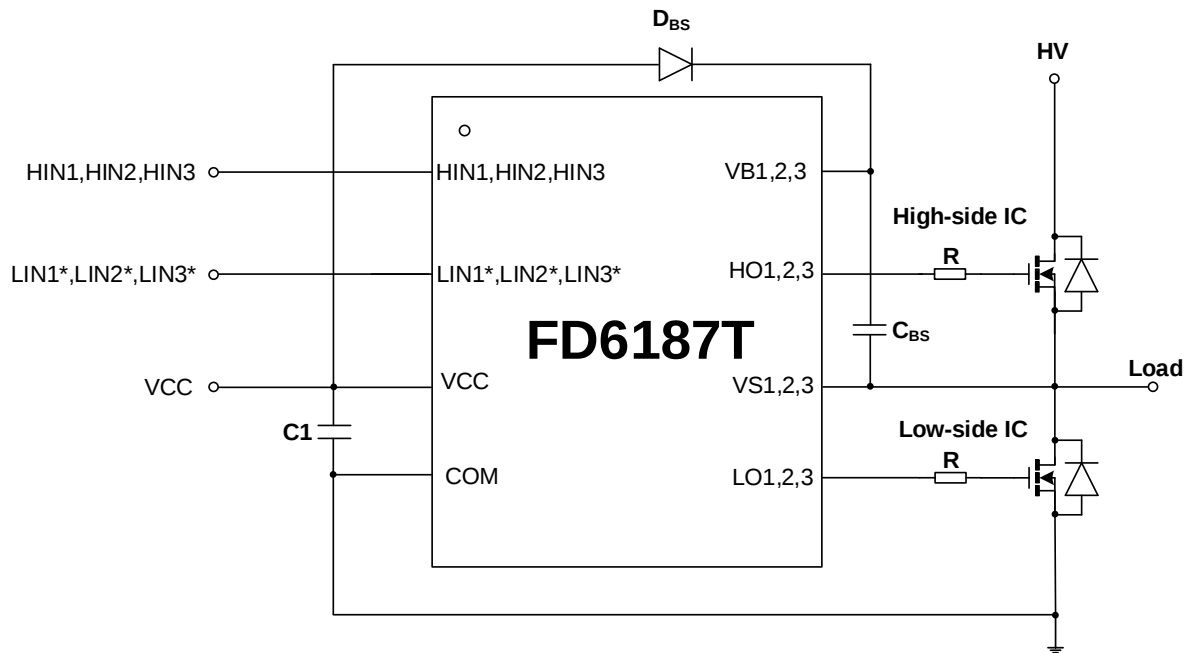


Figure 1-1 Typical Application Diagram of FD6187T

- C1: 10 μ F ~ 100 μ F power filter capacitor depending on the application circuit.
- R: Gate drive resistor. The resistance depends on deadtime and the device being driven.
- D_{BS}: Bootstrap diode. Those with high reverse breakdown voltage and short recovery time are preferred.
- C_{BS}: Bootstrap capacitor. 1 μ F ~ 100 μ F ceramic capacitor or tantalum capacitor is preferred.

Note: The above circuit and parameters are for reference only. The actual circuit shall be designed with the measured results.

1.6 Functional Block Diagram

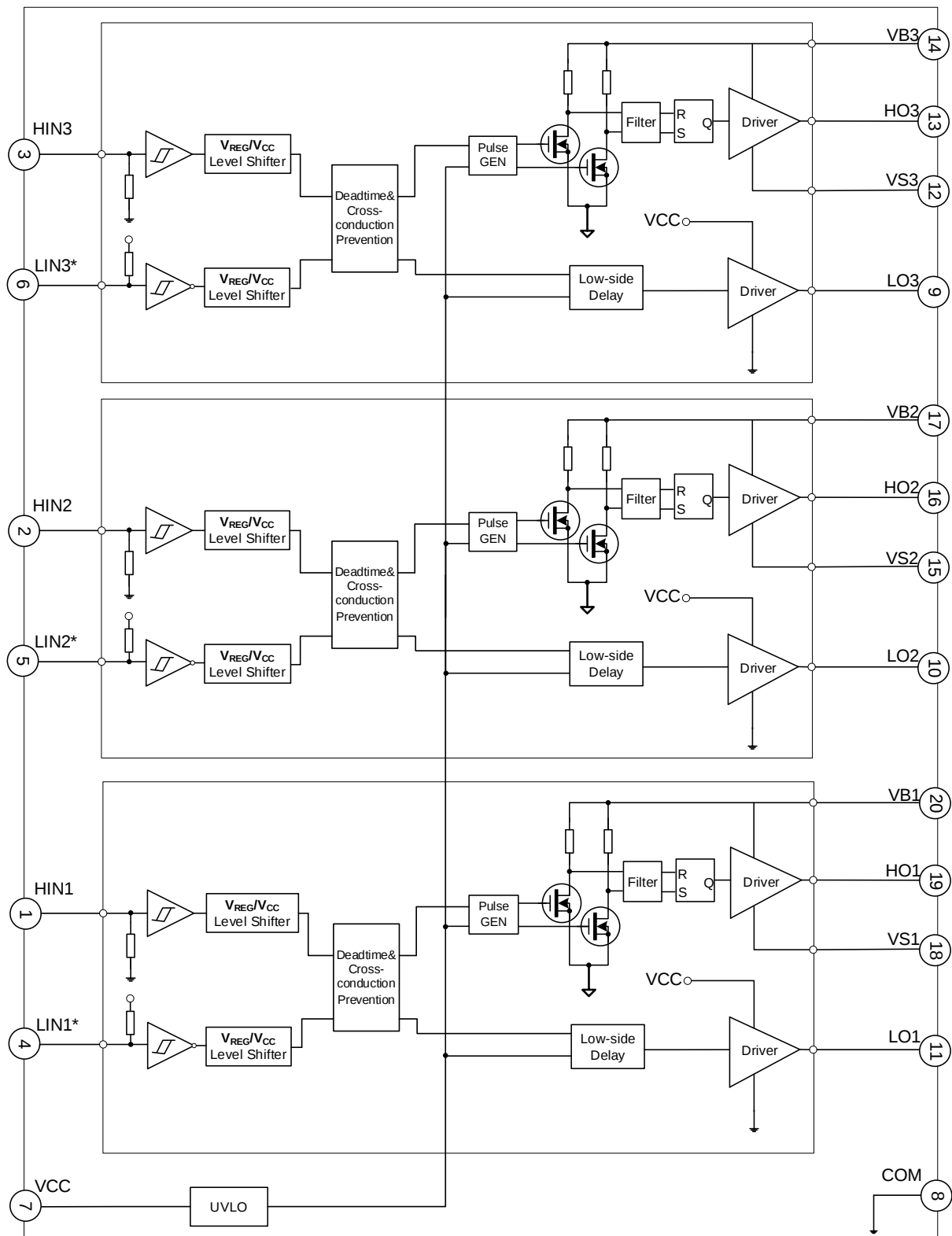


Figure 1-2 Functional Block Diagram of FD6187T

1.7 Pin Definitions

1.7.1 FD6187T TSSOP20 Pin Diagram

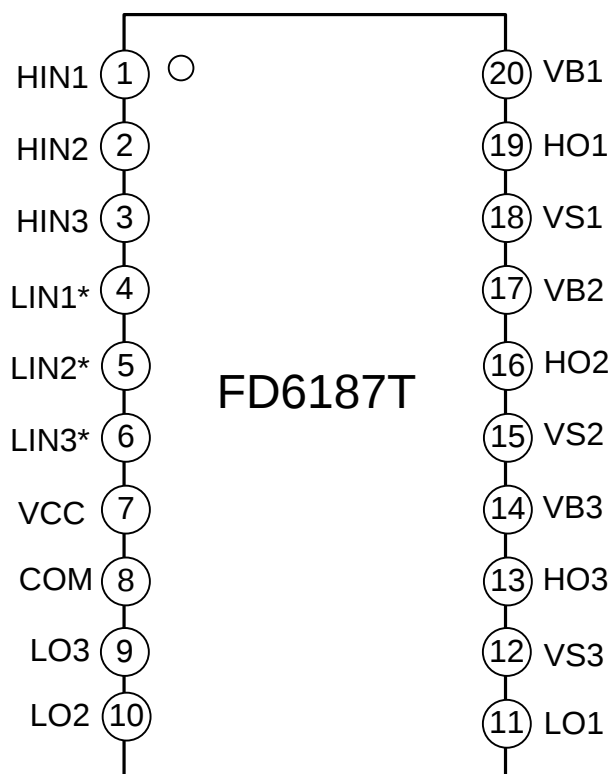


Figure 1-3 FD6187T TSSOP20 Pin Diagram

1.7.2 FD6187T TSSOP20 Pins

Table 1-1 FD6187T TSSOP20 Pin Descriptions

Pin	Name	Description
1, 2, 3	HIN1, HIN2, HIN3	High-side Input
4, 5, 6	LIN1*, LIN2*, LIN3*	Low-side Input
7	VCC	Low-side Supply Voltage
8	COM	Ground
9, 10, 11	LO3, LO2, LO1	Low-side Output
12, 15, 18	VS3, VS2, VS1	High-side Floating Offset Voltage
13, 16, 19	HO3, HO2, HO1	High-side Output
14, 17, 20	VB3, VB2, VB1	High-side Floating Absolute Voltage

2 Package Information

2.1 FD6187T TSSOP20

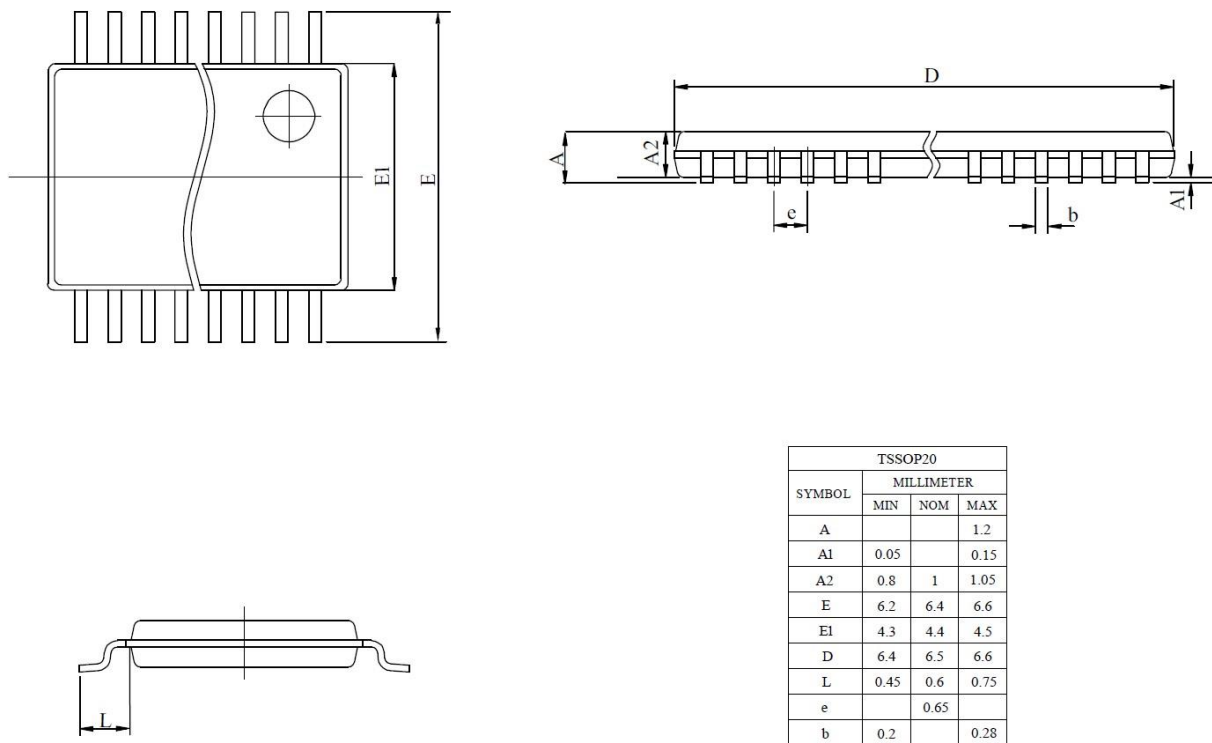


Figure 2-1 FD6187T TSSOP20 Package Drawings and Dimensions

Product Number	Package Type	Marking ID	Package Method	Quantity
FD6187T	TSSOP20	FD6187T	Tape & Reel	4000

3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Ratings

(All pins are referenced to COM unless otherwise specified)

Parameter		Symbol	Min. ~ Max.	Unit
High-side Floating Absolute Voltage		$V_{B1,2,3}$	-0.3 ~ 205	V
High-side Floating Offset Voltage		$V_{S1,2,3}$	$V_{B1,2,3} - 25 \sim V_{B1,2,3} + 0.3$	V
High-side Output Voltage		$V_{HO1,2,3}$	$V_{S1,2,3} - 0.3 \sim V_{B1,2,3} + 0.3$	V
Low-side Supply Voltage		V_{CC}	-0.3 ~ 25	V
Low-side Output Voltage		$V_{LO1,2,3}$	-0.3 ~ $V_{CC} + 0.3$	V
Logic Input Voltage (HIN, LIN*)		V_{IN}	-0.3 ~ $V_{CC} + 0.3$	V
Power Dissipation @ $T_A \leq 25^\circ\text{C}$	TSSOP20	P_D	≤ 1.25	W
Junction-to-ambient Thermal Resistance	TSSOP20	R_{thJA}	≤ 100	$^\circ\text{C/W}$
Junction Temperature		T_j	≤ 150	$^\circ\text{C}$
Storage Temperature		T_{stg}	-55 ~ 150	$^\circ\text{C}$

Notes:

- In any case, power dissipation shall not exceed P_D .
- The chip may get damaged if it operates at voltages exceeding those listed above.

3.2 Recommended Operating Conditions

Table 3-2 Recommended Operating Conditions^[1]

(All voltages are referenced to COM unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit
High-side Floating Absolute Voltage	$V_{B1,2,3}$	$V_{S1,2,3} + 4.0$	$V_{S1,2,3} + 22$	V
High-side Floating Offset Voltage	$V_{S1,2,3}$	-5	180	V
High-side Output Voltage	$V_{HO1,2,3}$	$V_{S1,2,3}$	$V_{B1,2,3}$	V
Low-side Supply Voltage	V_{CC}	5.0	22	V
Low-side Output Voltage	$V_{LO1,2,3}$	0	V_{CC}	V
Logic Input Voltage (HIN, LIN*)	V_{IN}	0	V_{CC}	V
Ambient Temperature	T_A	-40	125	$^\circ\text{C}$

Note:

[1] Exposure to recommended operating conditions for extended periods may affect device reliability.

3.3 Electrical Characteristics

Table 3-3 Electrical Characteristics

($T_A = 25^\circ\text{C}$, $V_{CC} = V_{BS1,2,3} = 15\text{V}$ and $V_{S1,2,3} = \text{COM}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Power Supply						
V_{CC} Quiescent Current	I_{QCC}	$V_{IN} = 0\text{V or } 5\text{V}$	-	330	500	μA
V_{BS} Quiescent Current	I_{QBS}	$V_{IN} = 0\text{V or } 5\text{V}$	-	70	120	μA
Leakage Current of Floating Power Supply	I_{LK}	$V_{B1,2,3} = V_{S1,2,3} = 180\text{V}$	-	0.1	5.0	μA
Input HIN/LIN*						
High-level Input Threshold Voltage	V_{IH}		2.7	2.1	-	V
Low-level Input Threshold Voltage	V_{IL}		-	1.4	0.8	V
LIN* High-level Input Bias Current	I_{LIN*+}	$V_{LIN*} = 0\text{V}$	-	25	50	μA
LIN* Low-level Input Bias Current	I_{LIN*-}	$V_{LIN*} = 5\text{V}$	-	-	4	μA
HIN High-level Input Bias Current	I_{HIN+}	$V_{HIN} = 5\text{V}$	-	25	50	μA
HIN Low-level Input Bias Current	I_{HIN-}	$V_{HIN} = 0\text{V}$	-	-	4	μA
HIN Input Pull-down Resistor	R_{HIN}		100	200	300	$\text{K}\Omega$
LIN* Input Pull-up Resistor	R_{LIN*}		100	200	300	$\text{K}\Omega$
UVLO						
V_{CC} UVLO Threshold Voltage	V_{CCUV+}		3.8	4.4	5.0	V
V_{CC} UVLO Release Voltage	V_{CCUV-}		3.5	4.1	4.7	V
V_{CC} UVLO Hysteresis Voltage	V_{CCUVH}		0.2	0.3	-	V
High-side/Low-side Output						
High-side Output Voltage	V_{OH}	$I_O = 100\text{mA}$	-	1.0	1.5	V
Low-side Output Voltage	V_{OL}	$I_O = 100\text{mA}$	-	0.5	0.75	V
High-level Output Short-circuit Pulsed Current	I_{OH}	$V_O = 0\text{V}$	0.5	0.8	-	A
Low-level Output Short-circuit Pulsed Current	I_{OL}	$V_O = 15\text{V}$	0.5	0.8	-	A
Time Parameters						
Turn-on Propagation Delay	t_{on}		-	180	300	ns
Turn-off Propagation Delay	t_{off}		-	70	130	ns
Turn-on Rise Time	t_r	$C_L = 1000\text{pF}$	-	30	70	ns
Turn-off Fall Time	t_f	$C_L = 1000\text{pF}$	-	30	70	ns
High-low Side Delay Match	MT		-	-	50	ns
Deadtime	DT		-	100	-	ns

4 Propagation Delay Test Standards

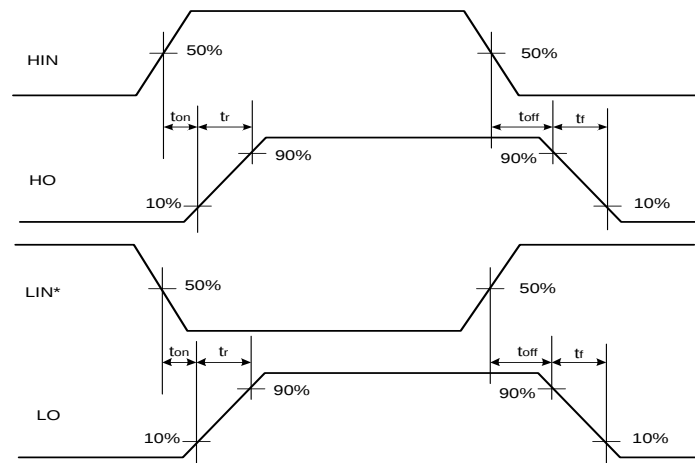


Figure 4-1 Propagation Delay Test Standards

5 Propagation Delay Matching Test Standards

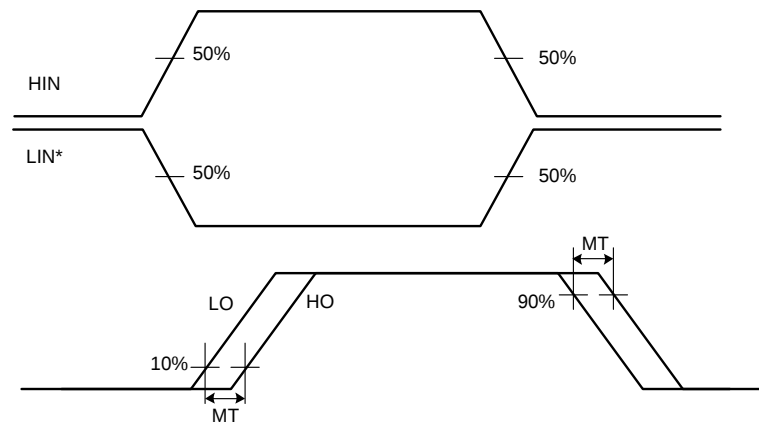


Figure 5-1 Propagation Delay Matching Test Standards

6 Cross-conduction Prevention

A protection circuit is specially designed inside the chip to enable cross-conduction prevention feature, which effectively prevents MOSFETs from damage when high-side and low-side input signals are interfered. The figure below shows how the protection circuit works.

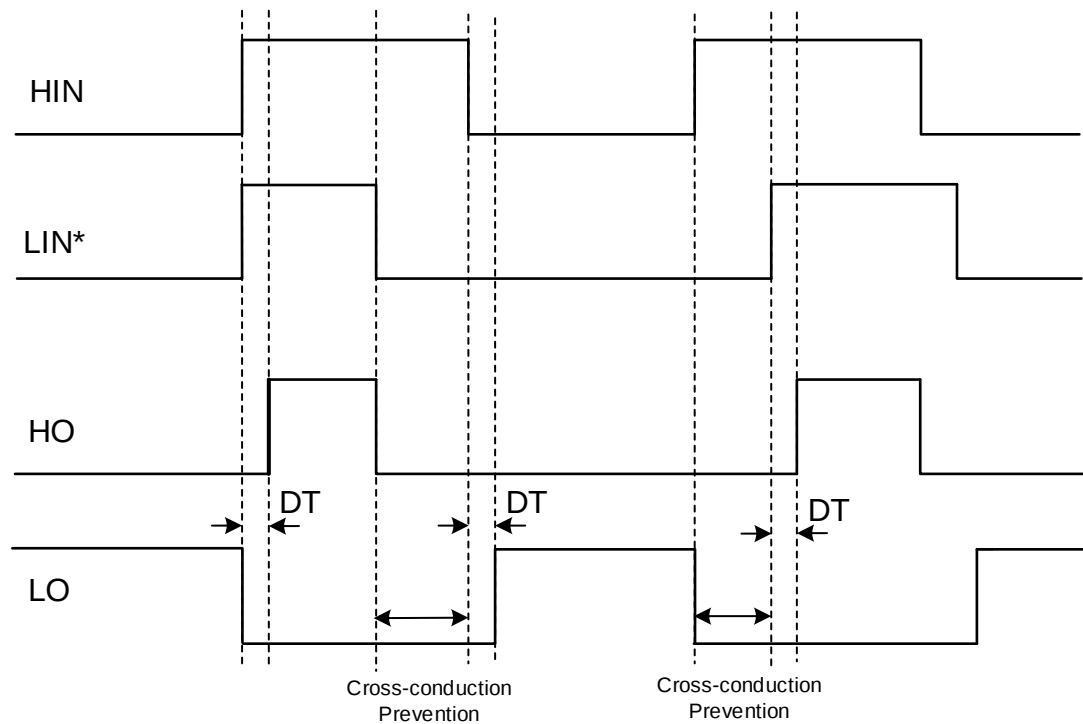


Figure 6-1 Schematic Diagram of Cross-conduction Prevention

7 Deadtime

The chip is designed with dedicated deadtime protection circuit. Both the high-side and low-side outputs are set to LOW during the deadtime. This feature prevents both MOSFETs of each half-bridge from switching on at the same time.

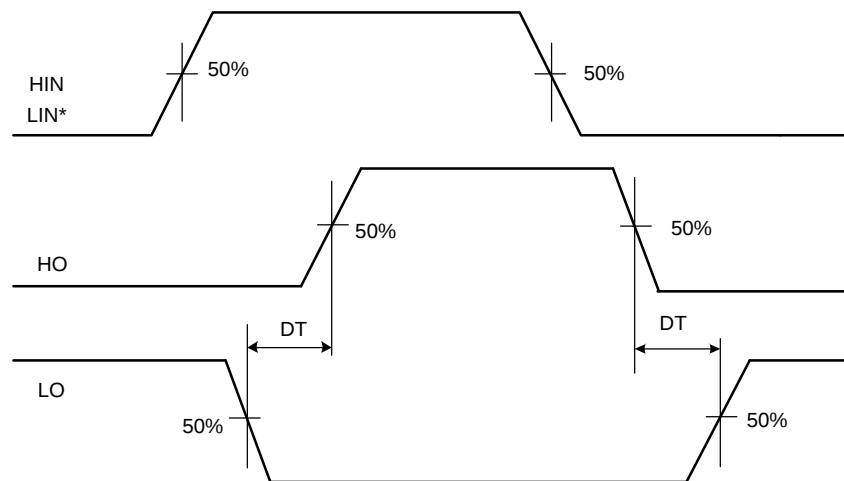


Figure 7-1 Schematic Diagram of Deadtime

8 Revision History

Rev.	Description	Date	Prepared By
V1.0	First release, translated from Chinese version 1.0	2024/01/19	Eric Deng

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